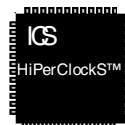


75MHZ, LVCMOS/LVTTL OSCILLATOR REPLACEMENT

ICS840-275

GENERAL DESCRIPTION

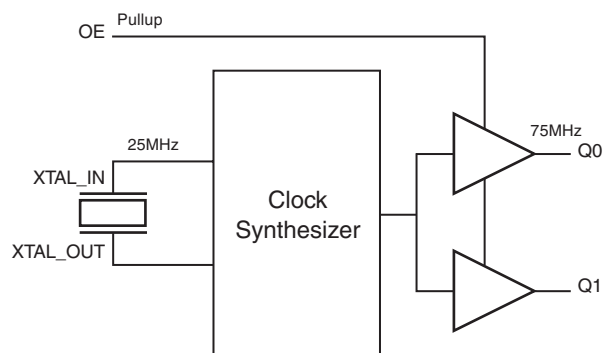


The ICS840-275 is a SAS/SATA Oscillator Replacement and a member of the HiPerClocks™ family of high performance devices from IDT. The ICS840-275 uses a 25MHz crystal to synthesize 75MHz. The ICS840-275 has excellent jitter performance. The ICS840-275 is packaged in a small 8-pin SOIC, making it ideal for use in systems with limited board space.

FEATURES

- Two LVCMOS/LVTTL output, 15Ω output impedance
- Crystal oscillator interface designed for 25MHz, 18pF parallel resonant crystal
- Output frequency: 75MHz
- Random jitter: 3ps (typical)
- Deterministic jitter: 0.2ps (typical)
- 3.3V operating supply
- 0°C to 70°C ambient operating temperature
- Available in both standard (RoHS 5) and lead-free (RoHS 6) packages

BLOCK DIAGRAM



PIN ASSIGNMENT

VDD	1	8	Q1
XTAL_OUT	2	7	Q0
XTAL_IN	3	6	VDDO
OE	4	5	GND

ICS840-275
8-Lead SOIC

3.90mm x 4.92mm x 1.37mm body package

M Package

Top View

The Preliminary Information presented herein represents a product in pre-production. The noted characteristics are based on initial product characterization and/or qualification. Integrated Device Technology, Incorporated (IDT) reserves the right to change any circuitry or specifications without notice.

TABLE 1. PIN DESCRIPTIONS

Number	Name	Type		Description
1	V _{DD}	Power		Power supply pin.
2, 3	XTAL_OUT, XTAL_IN	Input		Crystal oscillator interface. XTAL_IN is the input, XTAL_OUT is the output.
4	OE	Input	Pullup	Output enable pin. When HIGH, Qx outputs are enabled. When LOW, forces Qx outputs to HiZ state. LVCMOS/LVTTL interface levels.
5	GND	Power		Power supply ground.
6	V _{DDO}	Power		Output supply pin.
7, 8	Q0, Q1	Output		Single-ended clock outputs. LVCMOS/LVTTL interface levels. 15Ω output impedance.

NOTE: *Pullup* refers to internal input resistors. See Table 2, Pin Characteristics, for typical values.

TABLE 2. PIN CHARACTERISTICS

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C _{IN}	Input Capacitance			4		pF
R _{PULLUP}	Input Pullup Resistor			51		kΩ
R _{OUT}	Output Impedance			15		Ω

TABLE 3. CONTROL FUNCTION TABLE

Control Inputs	Output
OE	Q0, Q1
0	Hi-Z
1	Active

ABSOLUTE MAXIMUM RATINGS

Supply Voltage, V_{DD}	4.6V
Inputs, V_I	-0.5V to $V_{DD} + 0.5V$
Outputs, V_O	-0.5V to $V_{DDO} + 0.5V$
Package Thermal Impedance, θ_{JA}	112.7°C/W (0 lfpm)
Storage Temperature, T_{STG}	-65°C to 150°C

NOTE: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

TABLE 4A. POWER SUPPLY DC CHARACTERISTICS, $V_{DD} = V_{DDO} = 3.3V \pm 0.3V$, $T_A = -40^\circ\text{C}$ TO 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{DD}	Power Supply Voltage		3.0	3.3	3.6	V
V_{DDO}	Output Supply Voltage		3.0	3.3	3.6	V
I_{DD}	Power Supply Current	OE = V_{DD} (output enabled)			80	mA
I_{DDO}	Output Supply Current				20	mA

TABLE 4B. LVCMOS/LVTTL DC CHARACTERISTICS, $V_{DD} = V_{DDO} = 3.3V \pm 0.3V$, $T_A = -40^\circ\text{C}$ TO 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{IH}	Input High Voltage		2		$V_{DD} + 0.3$	V
V_{IL}	Input Low Voltage		-0.3		0.8	V
I_{IH}	Input High Current	$V_{DD} = V_{IN} = 3.6V$			5	μA
I_{IL}	Input Low Current	$V_{DD} = 3.6V$, $V_{IN} = 0V$	-150			μA
V_{OH}	Output High Voltage; NOTE 1		2.6			V
V_{OL}	Output Low Voltage; NOTE 1				0.5	V

NOTE 1: Outputs terminated with 50Ω to $V_{DDO}/2$. See Parameter Measurement Information Section, "3.3V Output Load Test Circuit".

TABLE 5. CRYSTAL CHARACTERISTICS

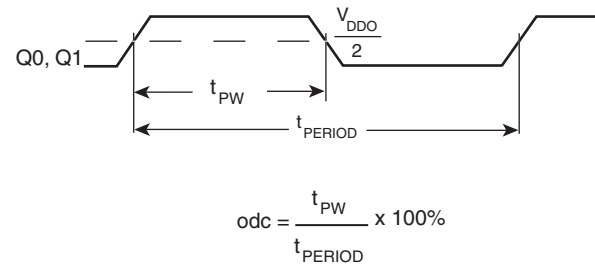
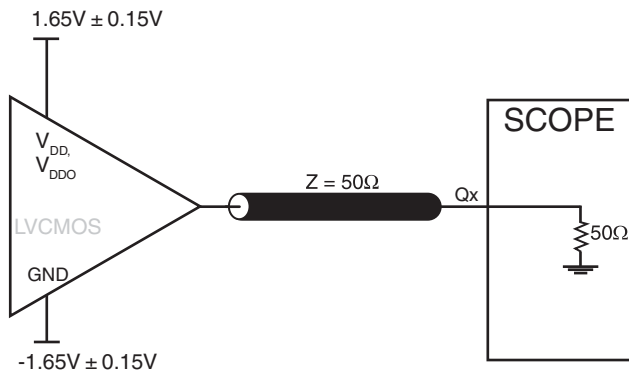
Parameter	Test Conditions	Minimum	Typical	Maximum	Units
Mode of Oscillation		Fundamental			
Frequency			25		MHz
Equivalent Series Resistance (ESR)				40	Ω
Shunt Capacitance				7	pF
Drive Level				300	μW

TABLE 6. AC CHARACTERISTICS, $V_{DD} = V_{DDO} = 3.3V \pm 0.3V$, $T_A = -40^{\circ}C$ TO $85^{\circ}C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f_{OUT}	Output Frequency			75		MHz
t_{DJ}	Deterministic Jitter; NOTE 1			0.2		ps
t_{RJ}	Random Jitter; NOTE 1			3		ps
t_{RMS}	RMS of Total Distribution (σ); NOTE 1			3		ps
t_{P-P}	Peak-to-Peak Jitter; NOTE 1			28		ps
t_{OSC}	Oscillation Start Up Time	Time at minimum operating voltage to be 0 s			10	ms
t_R / t_F	Output Rise/Fall Time	20% to 80%		700		ps
odc	Output Duty Cycle			50		%

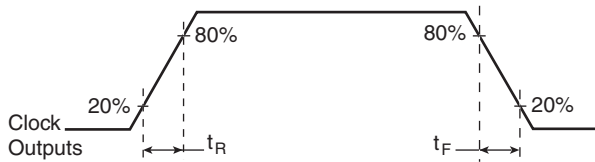
NOTE 1: Measured using Wavecrest SIA-3000.

PARAMETER MEASUREMENT INFORMATION



3.3V OUTPUT LOAD AC TEST CIRCUIT

OUTPUT DUTY CYCLE/PULSE WIDTH/PERIOD



OUTPUT RISE/FALL TIME

APPLICATION INFORMATION

RECOMMENDATIONS FOR UNUSED OUTPUT PINS

OUTPUTS:

LVCMOS OUTPUT:

All unused LVCMOS output can be left floating. We recommend that there is no trace attached.

CRYSTAL INPUT INTERFACE

The ICS840-275 has been characterized with 18pF parallel resonant crystals. The capacitor values, C1 and C2, shown in *Figure 1* below were determined using a 25MHz, 18pF parallel

resonant crystal and were chosen to minimize the ppm error. The optimum C1 and C2 values can be slightly adjusted for different board layouts.

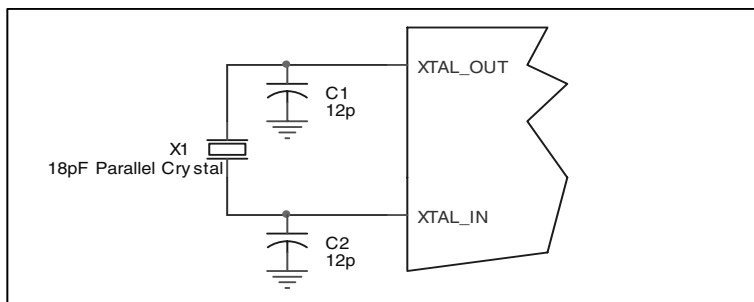


FIGURE 1. CRYSTAL INPUT INTERFACE

RELIABILITY INFORMATION

TABLE 7. θ_{JA} VS. AIR FLOW TABLE 8 LEAD SOIC

θ_{JA} by Velocity (Linear Feet per Minute)			
	0	200	500
Single-Layer PCB, JEDEC Standard Test Boards	153.3°C/W	128.5°C/W	115.5°C/W
Multi-Layer PCB, JEDEC Standard Test Boards	112.7°C/W	103.3°C/W	97.1°C/W
NOTE: Most modern PCB designs use multi-layered boards. The data in the second row pertains to most designs.			

TRANSISTOR COUNT

The transistor count for ICS840-275 is: 2423

PACKAGE OUTLINE - M SUFFIX FOR 8 LEAD SOIC

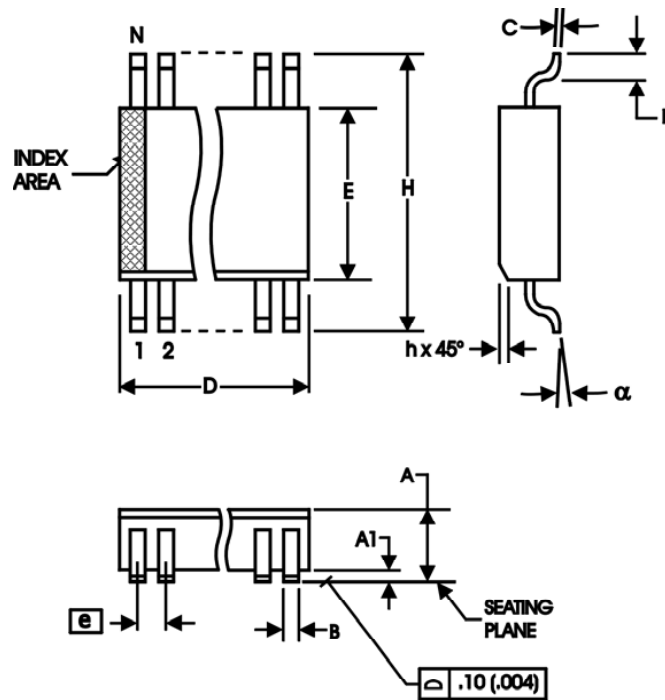


TABLE 8. PACKAGE DIMENSIONS

SYMBOL	Millimeters	
	MINIMUM	MAXIMUM
N	8	
A	1.35	1.75
A1	0.10	0.25
B	0.33	0.51
C	0.19	0.25
D	4.80	5.00
E	3.80	4.00
e	1.27 BASIC	
H	5.80	6.20
h	0.25	0.50
L	0.40	1.27
α	0°	8°

Reference Document: JEDEC Publication 95, MS-012

TABLE 9. ORDERING INFORMATION

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
ICS840AM-275	840AM275	8 lead SOIC	tube	0°C to 70°C
ICS840AM-275T	840AM275	8 lead SOIC	2500 tape & reel	0°C to 70°C
ICS840AM-275LF	TBD	8 lead "Lead-Free" SOIC	tube	0°C to 70°C
ICS840AM-275LFT	TBD	8 lead "Lead-Free" SOIC	2500 tape & reel	0°C to 70°C

NOTE: Parts that are ordered with an "LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant.

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